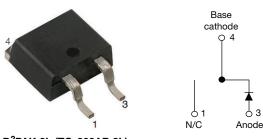


1200 V Gen 4 Power Silicon Carbide Schottky Diode, 5 A



D²PAK 2L (TO-263AB 2L)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)}	5 A					
V_R	1200 V					
V _F at I _F at 25 °C, typ.	1.35 V					
T _J max.	175 °C					
I _R at V _R at 175 °C	76 µA					
Q _C (V _R = 400 V)	27 nC					
Package	D ² PAK 2L (TO-263AB 2L)					
Circuit configuration	Single					

FEATURES

Positive V_F temperature coefficient for easy paralleling



• Virtually no recovery tail and no switching losses

Temperature invariant switching behavior

COMPLIANT HALOGEN FREE

- Tomporatare invariant ownering benevior
- 175 °C maximum operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Meets JESD 201 class1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high-speed hard switching across a wide temperature range. This SiC diode is ideal for demanding applications such as high efficiency PFC diodes and ultra-high frequency output rectifiers in AC/DC and DC/DC converters.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS			
Peak repetitive reverse voltage	V_{RRM}		1200	V			
Continuous famueral surrent	I _F ⁽¹⁾	$I_F^{(1)}$ $T_C = 158 ^{\circ}\text{C (DC)}$		Α			
Continuous forward current	I _F ⁽²⁾	T _C = 153 °C (DC)	5	Α			
DC blocking voltage	V_{DC}		1200	V			
Repetitive peak forward current	epetitive peak forward current I _{FRM}		26				
New venetitive needs femiliard evident	I _{FSM}	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	40	Α			
Non-repetitive peak forward surge current		$T_C = 110 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, half sine wave	30				
	P _{tot} (1)	T _C = 25 °C	86	w			
Dawar dissination		T _C = 110 °C	37	T VV			
Power dissipation	P _{tot} (2)	T _C = 25 °C	62.5	W			
		T _C = 110 °C	27				
124	∫i ² dt	T _C = 25 °C	8				
I ² t value		T _C = 110 °C	4.5	- A ² s			
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C			

Notes

- (1) Based on typical R_{th}
- (2) Based on maximum R_{th}
- (3) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta,JA}$



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS	
		I _F = 5 A	-	1.35	1.6		
Forward voltage	V _F	I _F = 5 A, T _J = 150 °C	-	1.74	2	٧	
		I _F = 5 A, T _J = 175 °C	-	1.87	-		
Reverse leakage current	I _R	$V_R = V_R$ rated	-	2.4	80	μA	
		V _R = V _R rated, T _J = 150 °C	-	36	190		
		V _R = V _R rated, T _J = 175 °C	-	76	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	300	-	nE	
		V _R = 800 V, f = 1 MHz	-	19	-	pF	
Total capacitive charge	Q _C	V _R = 800 V, f = 1 MHz	-	27	-	nC	

THERMAL AND MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS						
Thermal resistance, junction to case	R _{thJC}		-	1.75	2.4	°C/W	
Marking device	4C05ET12S						

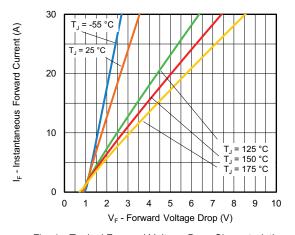


Fig. 1 - Typical Forward Voltage Drop Characteristics

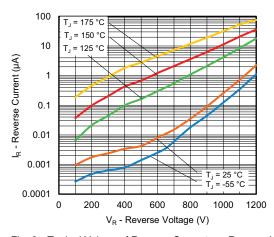


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

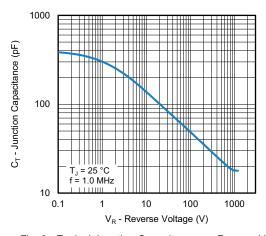


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

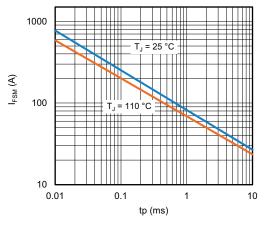


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

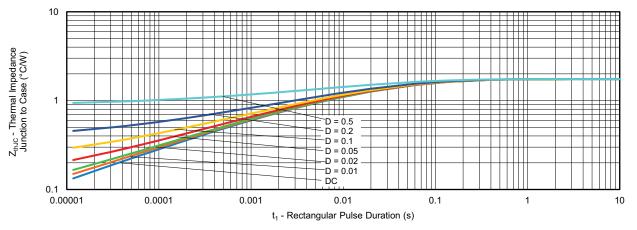


Fig. 5 - Typical Thermal Impedance Z_{thJC} Characteristics

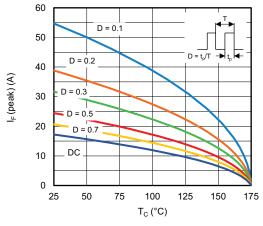


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

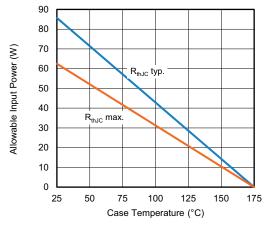


Fig. 7 - Forward Power Loss Characteristics

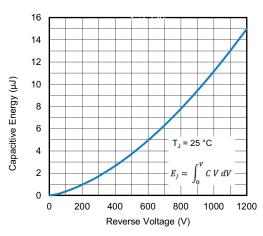


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

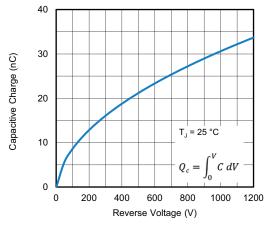
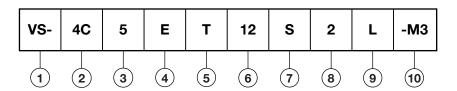


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - 4C = SiC diode, generation 4

Current rating (10 = 10 A)

4 - E = single diode

T = D²PAK package

6 - Voltage rating: (12 = 1200 V)

7 - S = surface mountable

9 - L = tape and reel (left oriented)

10 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

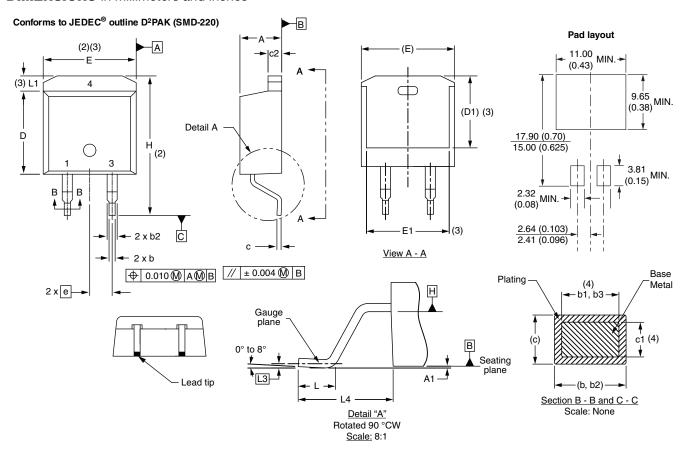
ORDERING INFORMATION							
PREFERRED P/N	UNIT WEIGHT	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-4C05ET12S2L-M3	2 g	800 per reel	13" diameter reel				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96683			
Part marking information	www.vishay.com/doc?96693			
Packaging information	www.vishay.com/doc?95032			



D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIMETERS		INC	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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